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View Online at https://aerobasegroup.com/nsn/5961-01-067-3030
Inclosure Material:
Metal
Overall Length:
Between 0.250 inches and 0.340 inches
Overall Diameter:
0.620 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-66
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case and mounting hardware
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
12.0 emitter to base voltage, dc and 150.0 collector to base voltage, dc and 150.0 collector to emitter reverse voltage
Current Rating Per Characteristic:
Between 0.50 amperes source cutoff current and 5.00 amperes source cutoff current
Power Rating Per Characteristic:
2.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: npn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
1 case and 3 pin
Specification Data:
81349-mil-s-19500/472 government specification
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

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